IC Knowledge – 2010 IC Cost Model Supported Processes List

January 1, 2010 the following processes are included in the 2009 IC Cost Model. The syntax is: wafer size (mm) – linewidth (nm) – process type and or company – polysilicon layers – metal layers and type. Processes are in order of wafer size (smallest to largest), linewidth (largest to smallest), process type and or company (alphabetical order), poly layers (least to most) and metal layers (least to most)

1. 100mm - 3.0µm - Bipolar - 2 layer aluminum
2. 100mm - 3.0µm - CMOS - 1 layer poly - 1 layer aluminum
3. 100mm - 2.0µm - CMOS - 1 layer poly - 2 layer aluminum
4. 100mm - 2.0µm - NMOS - 1 layer poly - 2 layer aluminum
5. 125mm - 3.0µm - Bipolar - 2 layer aluminum
6. 125mm - 2.0µm - NXP - Bipolar - 2 layer aluminum
7. 125mm - 2.0µm - CMOS - 1 layer poly - 2 layer aluminum
8. 125mm - 1.2µm - BiCMOS - 1 layer poly - 2 layer aluminum
9. 125mm - 1.0µm - NXP - BCDMOS - 2 layer aluminum
10. 150mm - 5.0µm - Infineon - Bipolar - 2 layer aluminum
11. 150mm - 4.0µm - Polar Fab - BP14 Bipolar - 1 layer aluminum
12. 150mm - 4.0µm - Polar Fab - BP14 Bipolar - 2 layer aluminum
13. 150mm - 3.0µm - Bipolar - 2 layer aluminum
14. 150mm - 3.0µm - Denso - BiCMOS on SOI - 3 layer aluminum
15. 150mm - 2.5µm - X-Fab - DIMOST 500V SOI BCD - 1 poly layer - 2 aluminum layers
16. 150mm - 2.0µm - Bipolar - 2 layer aluminum
17. 150mm - 2.0µm - CMOS logic - 1 layer poly - 2 layer aluminum
18. 150mm - 1.5µm - CMOS - 1 layer poly - 2 layer aluminum
19. 150mm - 1.5µm - Polar Fab - PBC3 60V BCDMOS - 1 layer poly - 2 layer aluminum
20. 150mm - 1.25µm - Polar Fab - BP30 30V Bipolar - 1 layer aluminum
21. 150mm - 1.25µm - Polar Fab - BP30 30V Bipolar - 2 layer aluminum
22. 150mm - 1.2µm - AMI - CA BiCMOS - 1 layer poly - 2 layer aluminum
23. 150mm - 1.2µm - Bosch - BCDMOS - 1 layer poly - 3 layer aluminum.
24. 150mm - 1.2µm - Bosch - BCDMOS - 2 layer poly - 3 layer aluminum.
25. 150mm - 1.2µm - Bosch - CMOS - 1 layer poly - 3 layer aluminum.
26. 150mm - 1.2µm - CMOS logic - 1 layer poly - 2 layer aluminum
27. 150mm - 1.2µm - Denso - BiCMOS on SOI - 3 layer aluminum
28. 150mm - 1.0µm - Bosch - BCDMOS - 1 layer poly - 3 layer aluminum.
29. 150mm - 1.0µm - Bosch - BCD3s BCDMOS - 2 layer poly - 3 layer aluminum.
30. 150mm - 1.0µm - Bosch - CMOS - 1 layer poly - 3 layer aluminum.
31. 150mm - 1.0µm - STMicro - BCDMOS - 1 layer poly - 3 layer aluminum.
32. 150mm - 1.0µm - STMicro - CMOS - 1 layer poly - 2 layer aluminum.
33. 150mm - 1.0µm - Tower - TS100 CMOS logic - 1 layer poly - 2 layer aluminum
34. 150mm - 1.0µm - TSMC - HVCMOS - 1 layer poly - 2 layer metal
35. 150mm - 1.0µm - X-Fab - XD10H 650V SOI BCD - 3 layer poly - 3 layer aluminum
36. 150mm - 1.0µm - X-Fab - XC10 Mixed Signal CMOS - 2 layer poly - 2 layer aluminum - pressure sensor

37. 150mm - 800nm - ASMC - BiCMOS - 1 layer poly - 3 layer aluminum
38. 150mm - 800nm - Bosch - BCDMOS - 1 layer poly - 3 layer aluminum.
39. 150mm - 800nm - Bosch - CMOS - 1 layer poly - 3 layer aluminum
40. 150mm - 800nm - CMOS logic - 1 layer poly - 2 layer aluminum
41. 150mm - 800nm - CMOS logic - 1 layer poly - 3 layer aluminum
42. 150mm - 800nm - Freescale - SMOS5 - 1 layer poly - 2 layer aluminum
43. 150mm - 800nm - Polar Fab - ABC3 BiCMOS - 1 layer poly - 2 layer aluminum
44. 150mm - 800nm - Polar Fab - ABC3 BiCMOS - 1 layer poly - 3 layer aluminum
45. 150mm - 800nm - Polar Fab - RFBC RF BiCMOS - 2 layer poly - 2 layer aluminum
46. 150mm - 800nm - Polar Fab - RFBC RF BiCMOS - 2 layer poly - 3 layer aluminum
47. 150mm - 800nm - STMicro - BCDMOS - 1 layer poly - 3 layer aluminum.
48. 150mm - 800nm - STMicro - CMOS - 1 layer poly - 3 layer aluminum.
49. 150mm - 800nm - Tower - TS80M CMOS logic - 2 layer poly - 3 layer aluminum
50. 150mm - 800nm - X-Fab - CX08 Mixed Signal HV CMOS w EEPROM - 2 layer poly - 3 layer aluminum
51. 150mm - 700nm - AMI - I2T30 30V BICMOS - 1 layer poly - 2 layer aluminum
52. 150mm - 700nm - AMI - I2T30E 30V BICMOS - 2 layer poly - 2 layer aluminum
53. 150mm - 700nm - AMI - I2T60 60V BICMOS - 2 layer poly - 2 layer aluminum
54. 150mm - 700nm - AMI - I2T100 100V BICMOS - 2 layer poly - 2 layer aluminum
55. 150mm - 700nm - Bosch - HC65 DOT BCDMOS - 2 layer poly - 3 layer aluminum.
56. 150mm - 600nm - ADI - EP135 - CBiCMOS - poly-poly cap - 3 layer aluminum with thin film resistor
57. 150mm - 600nm - ST Micro - 80V BCD5 - 2 layer poly - 3 layer aluminum
58. 150mm - 600nm - Tower - TS60M CMOS logic - 2 layer poly - 3 layer aluminum
59. 150mm - 600nm - TSMC - CMOS - 1 layer poly - 2 layer aluminum
60. 150mm - 600nm - TSMC - HVCMOS - 1 layer poly - 2 layer aluminum
61. 150mm - 600nm - X-Fab - CX06 CMOS logic - 1 layer poly - 3 layer aluminum
62. 150mm - 600nm - X-Fab - XB06 BiCMOS - 2 layer poly - 3 layer aluminum
63. 150mm - 600nm - X-Fab - XC06 HV CMOS with Flash - 2 layer poly - 3 layer aluminum
64. 150mm - 500nm - Polar Fab - PBC4 40V BCDMOS - 2 layer poly - 2 layer aluminum
65. 150mm - 500nm - Polar Fab - PBC4 40V BCDMOS - 2 layer poly - 3 layer aluminum
66. 150mm - 500nm - TI - BiCMO2 - CBiCMOS - 3 layer aluminum with thin film resistors
67. 150mm - 500nm - Tower - TS50 CMOS Logic - 2 layer poly - 3 layer aluminum
68. 150mm - 500nm - TSMC - CMOS - 1 poly layer - 3 aluminum layers
69. 150mm - 500nm - UMC - CMOS - 1 poly layer - 3 aluminum layers
70. 150mm - 450nm - NXP - BiMOS3 - 1 layer poly - 2 layer aluminum
71. 150mm - 350nm - AMI - I3T50 BCDMOS - 1 layer poly - 3 layer aluminum - MIM cap
72. 150mm - 350nm - AMI - I3T50 BCDMOS - 1 layer poly - 4 layer aluminum - MIM cap
73. 150mm - 350nm - AMI - I3T50 BCDMOS - 1 layer poly - 5 layer aluminum - MIM cap
74. 150mm - 350nm - Tower - TS35 CMOS Logic - 2 layer poly - 4 layer aluminum
75. 200mm - 800nm - CMOS logic - 1 layer poly - 2 layer aluminum
76. 200mm - 800nm - CMOS logic - 1 layer poly - 3 layer aluminum
77. 200mm - 800nm - Maxim - CB4 - CBiCMOS - vanadium schottky - 3 layer gold with thin film resistors
78. 200mm - 800nm - NXP - ABCD3 - 1 layer poly - 3 layer aluminum
79. 200mm - 700nm - CMOS logic - 1 layer poly - 3 layer aluminum
80. 200mm - 700nm - TI - LBC4 - 2 layer poly - 3 layer aluminum
81. 200mm - 600nm - Chartered - Analog CMOS - 2 layer poly - 3 layer aluminum
82. 200mm - 600nm - Chartered - BiCMOS - 2 layer poly - 2 layer aluminum
83. 200mm - 600nm - Chartered - BiCMOS - 2 layer poly - 3 layer aluminum
84. 200mm - 600nm - Chartered - Digital CMOS - 1 layer poly - 3 layer aluminum

85. 200mm - 500nm - BiCMOS - 1 layer poly - 3 layer aluminum
86. 200mm - 500nm - Chartered - CMOS - 1 layer poly - 3 layer aluminum
87. 200mm - 500nm - CMOS logic - 1 layer poly - 2 layer aluminum
88. 200mm - 500nm - CMOS logic - 1 layer poly - 3 layer aluminum
89. 200mm - 500nm - CMOS logic - 1 layer poly - 4 layer aluminum
90. 200mm - 500nm - Freescale - dual gate ox CMOS Logic w Flash - 2 layer poly - 2 layer aluminum
91. 200mm - 500nm - Micronas - RFCMOS - 2 layer poly - 2 layer aluminum
92. 200mm - 500nm - Polar Fab - PBC4 40V BCDMOS - 2 layer poly - 2 layer aluminum
93. 200mm - 500nm - Polar Fab - PBC4 40V BCDMOS - 2 layer poly - 3 layer aluminum
94. 200mm - 500nm - TSMC - CMOS - 1 poly layer - 3 aluminum layers
95. 200mm - 500nm - UMC - CMOS - 1 poly layer - 3 aluminum layers
96. 200mm - 350nm - ASMC - BiCMOS with EEPROM - 2 layer poly - 3 layer aluminum
97. 200mm - 350nm - ASMC - CMOS with EEPROM - 2 layer poly - 5 layer aluminum
98. 200mm - 350nm - BiCMOS logic - 1 layer poly - 5 layer aluminum
99. 200mm - 350nm - BiCMOS logic - 1 layer poly - 6 layer aluminum
100. 200mm - 350nm - Chartered - CMOS logic - 1 layer poly - 4 layer aluminum
101. 200mm - 350nm - Chartered - dual gate ox CMOS logic- 1 layer poly - 3 layer aluminum
102. 200mm - 350nm - Chartered - dual gate ox CMOS logic- 1 layer poly - 4 layer aluminum
103. 200mm - 350nm - Chartered - dual gate ox mixed signal CMOS - 2 layer poly - 4 layer aluminum
104. 200mm - 350nm - CMOS logic - 1 layer poly - 3 layer aluminum
105. 200mm - 350nm - CMOS logic - 1 layer poly - 4 layer aluminum
106. 200mm - 350nm - CMOS logic - 1 layer poly - 5 layer aluminum
107. 200mm - 350nm - CMOS logic - 1 layer poly - 6 layer aluminum
108. 200mm - 350nm - DRAM - 4 layer poly - 2 layer aluminum
109. 200mm - 350nm - Freescale - SMOS7 - 1 layer poly - 3 aluminum layers
110. 200mm - 350nm - HeJian - CMOS with Flash - 2 layer poly - 5 layer aluminum
111. 200mm - 350nm - Intel - BiCMOS logic - 1 layer poly - 4 layer aluminum
112. 200mm - 350nm - Intel - CMOS logic - 1 layer poly - 4 layer aluminum
113. 200mm - 350nm - NXP - CMOS logic with Flash - 2 layer poly - 5 layer aluminum
114. 200mm - 350nm - Polar Fab - BiCMOS Polar 35 - 2 layer poly - 2 layer aluminum
115. 200mm - 350nm - Polar Fab - BiCMOS Polar 35 - 2 layer poly - 3 layer aluminum
116. 200mm - 350nm - SMIC - CMOS - 1 layer poly - 4 layer aluminum
117. 200mm - 350nm - STMicro - BCD6 - 1 layer poly - 3 layer aluminum
118. 200mm - 350nm - STMicro - BCD6 - 1 layer poly - 4 layer aluminum
119. 200mm - 350nm - STMicro - BCD6 - 1 layer poly - 5 layer aluminum
120. 200mm - 350nm - TI - CMOS logic with Flash - 2 layer poly - 3 layer aluminum
121. 200mm - 350nm - TI - LBC5 - 2 layer poly - 3 layer aluminum
122. 200mm - 350nm - TSMC - CMOS - 1 layer poly - 4 layer aluminum
123. 200mm - 350nm - UMC - CMOS - 1 layer poly - 4 layer aluminum
124. 200mm - 350nm - X-Fab - LV CMOS with EEPROM and Schottky - 2 layer poly - 4 layer aluminum
125. 200mm - 350nm - X-Fab - Mixed Signal CMOS - 2 layer poly - 4 layer aluminum
126. 200mm - 300nm to 350nm - SRAM - 2 layer poly - 2 layer aluminum
127. 200mm - 300nm to 350nm - SRAM - 4 layer poly - 2 layer aluminum
128. 200mm - 250nm - Chartered - dual gate oxide CMOS logic - 1 layer poly - 5 layer aluminum
129. 200mm - 250nm - DRAM - 4 layer poly - 2 layer aluminum
130. 200mm - 250nm - Freescale - CMOS logic with Flash - 2 poly layers - 3 aluminum layers
131. 200mm - 250nm - Freescale - CMOS logic with Flash - 2 poly layers - 4 aluminum layers

132. 200mm - 250nm - Freescale - SMOS8 - 1 poly layer - 4 aluminum layers
133. 200mm - 250nm - HeJian - CMOS with Flash - 2 layer poly - 5 layer aluminum
134. 200mm - 250nm - Infineon - SiGe - 2 layer poly - 3 layer aluminum with MIM capacitors
135. 200mm - 250nm - Intel - CMOS logic - 1 layer poly - 5 layer aluminum
136. 200mm - 250nm - Intel - ETOX VI Flash - 2 layer poly - 2 layer aluminum
137. 200mm - 250nm - Qimonda trench DRAM - 1 tungsten plus 2 alminum layers
138. 200mm - 250nm - RFCMOS - 1 layer poly - 4 layer aluminum with MIM capacitor
139. 200mm - 250nm - SMIC - dual gate ox CMOS logic - 1 layer poly - 5 layer aluminum
140. 200mm - 250nm - SRAM - 5 layer poly - 3 layer aluminum
141. 200mm - 250nm - TI - LBC7 BiCMOS - 2 layer poly - 3 layer aluminum
142. 200mm - 250nm - Toshiba - NAND Flash - 4 layer poly - 1 tungsten and 2 aluminum layers
143. 200mm - 250nm - TSMC - single gate ox CMOS logic - 1 layer poly - 3 layer aluminum
144. 200mm - 250nm - TSMC - dual gate ox CMOS logic - 1 layer poly - 4 layer aluminum
145. 200mm - 250nm - TSMC - dual gate ox CMOS logic - 1 layer poly - 5 layer aluminum
146. 200mm - 250nm - TSMC - single gate ox CMOS logic - 1 layer poly - 6 layer aluminum
147. 200mm - 250nm - UMC - dual gate ox CMOS logic - 1 layer poly - 5 layer aluminum
148. 200mm - 220nm - Infineon - dual gate ox CMOS logic - 2 layer poly - 5 layer aluminum with Flash
149. 200mm - 180nm - Chartered - dual gate oxide CMOS logic - 1 layer poly - 6 layer aluminum
150. 200mm - 180nm - Chartered - Mixed Signal RF CMOS - 1 layer poly - 6 layer aluminum
151. 200mm - 180nm - DRAM - 4 layer poly - 3 layer aluminum
152. 200mm - 180nm - Freescale - dual gate ox RFCMOS - 1 layer poly - 4 layer copper with MIM
153. 200mm - 180nm - Freescale - dual gate ox SOI CMOS - 1 layer poly - 7 layer aluminum
154. 200mm - 180nm - HeJian - CMOS with Flash - 2 layer poly - 5 layer aluminum
155. 200mm - 180nm - IBM - 7HP SiGe BiCMOS - 6 layer copper with single MIM and TaN resistor
156. 200mm - 180nm - IBM - 7RF RF CMOS - 3 layer Cu + 3 layer Al with single MIM and TaN resistor
157. 200mm - 180nm - IBM - 7SF dual gate ox CMOS Logic - 1 layer poly - 4 layer copper
158. 200mm - 180nm - IBM - 7SF dual gate ox CMOS Logic - 1 layer poly - 5 layer copper
159. 200mm - 180nm - IBM - 7SF dual gate ox CMOS Logic - 1 layer poly - 6 layer copper
160. 200mm - 180nm - IBM - 7WL SiGe BiCMOS - 3 layer Cu + 3 layer Al with single MIM and TaN resistor
161. 200mm - 180nm - IBM - eDRAM - 4 layer poly - 5 layer copper
162. 200mm - 180nm - IBM - eDRAM - 4 layer poly - 6 layer copper
163. 200mm - 180nm - Infineon - dual gate ox CMOS Logic - 1 layer poly - 4 layer copper w 1 aluminum layer + fuses
164. 200mm - 180nm - Intel - CMOS Logic - 1 layer poly - 6 layer aluminum - FSG ILD
165. 200mm - 180nm - Intel - ETOX VII Flash - 2 layer poly - 3 layer aluminum
166. 200mm - 180nm - NEC - dual gate ox CMOS logic - 1 layer poly - 5 aluminum layers
167. 200mm - 180nm - NXP - dual gate ox CMOS Logic - 1 poly layer - 1 tungsten and 6 aluminum layers
168. 200mm - 180nm - Renesas - CMOS Logic with Flash - 2 poly layers - 4 aluminum layers
169. 200mm - 180nm - Samsung - SRAM - 1 poly layer - 4 aluminum layers
170. 200mm - 180nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 6 layer aluminum - FSG ILD
171. 200mm - 180nm - SRAM - 5 layer poly - 3 layer aluminum
172. 200mm - 180nm - SSMC - dual gate ox CMOS logic - 1 poly layer - 6 aluminum layers - FSG ILD

173. 200mm - 180nm - STMicro - BCD8 - 1 layer poly - 4 aluminum layers - FSG
174. 200mm - 180nm - STMicro - BCD8 - 1 layer poly - 5 aluminum layers - FSG
175. 200mm - 180nm - STMicro - BCD8 - 1 layer poly - 6 aluminum layers - FSG
176. 200mm - 180nm - TI - CMOS Logic with Flash - 2 layer poly - 4 layer aluminum - FSG ILD
177. 200mm - 180nm - TI - CMOS Logic - 1 layer poly - 5 layer aluminum - FSG ILD
178. 200mm - 180nm - TI - CMOS Logic - 1 layer poly - 5 layer copper - FSG ILD
179. 200mm - 180nm - Toshiba - dual gate oxide CMOS logic - 1 layer poly - 4 layer aluminum
180. 200mm - 180nm - Tower - TS18SL dual gate oxide CMOS logic - 1 layer poly - 6 layer aluminum - FSG ILD
181. 200mm - 180nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 5 layer aluminum - FSG ILD
182. 200mm - 180nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer aluminum - FSG ILD
183. 200mm - 180nm - TSMC - dual gate ox CMOS Logic with FLASH - 1 layer poly - 6 layer aluminum - FSG ILD
184. 200mm - 180nm - TSMC - dual gate RFCMOS - 1 layer poly - 4 layer aluminum - FSG ILD
185. 200mm - 180nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 5 layer aluminum - FSG ILD
186. 200mm - 180nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer aluminum - FSG ILD
187. 200mm - 170nm - Infineon - NAND Flash - 1 layer poly - 1 tungsten and 2 aluminum layers
188. 200mm - 170nm - Toshiba - NAND Flash - 4 layer poly - 1 tungsten and 2 aluminum layers
189. 200mm - 160nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 6 layer aluminum - FSG ILD
190. 200mm - 160nm - Tower - dual gate ox CMOS Logic - 1 layer poly - 5 layer aluminum - FSG
191. 200mm - 150nm - Chartered - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
192. 200mm - 150nm - Micron - CMOS image sensor - 2 layer poly - 5 aluminum layers
193. 200mm - 150nm - Samsung - NAND Flash - 4 layer poly - 1 tungsten and 1 aluminum layer
194. 200mm - 150nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
195. 200mm - 150nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 5 layer copper with aluminum bond pads - FSG ILD
196. 200mm - 150nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
197. 200mm - 150nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
198. 200mm - 150nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer aluminum - FSG ILD
199. 200mm - 150nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer aluminum - FSG ILD
200. 200mm - 140nm - Toshiba - TC260 dual gate ox CMOS with trench DRAM - 7 layer copper
201. 200mm - 130nm - Chartered - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
202. 200mm - 130nm - DRAM - 4 layer poly - 3 layer aluminum
203. 200mm - 130nm - Fujitsu - PLD process - 8 copper layers with 1 aluminum layer

204. 200mm - 130nm - IBM - 8HP SiGe BiCMOS - 6 layer copper with single MIM and TaN resistor
205. 200mm - 130nm - IBM - 8HP SiGe BiCMOS - 7 layer copper with single MIM and TaN resistor
206. 200mm - 130nm - IBM - 8HP SiGe BiCMOS - 8 layer copper with single MIM and TaN resistor
207. 200mm - 130nm - IBM - 8RF RF CMOS - with Cu-Cu-Cu-Al-CU-Al and single MIM and TaN resistor
208. 200mm - 130nm - IBM - 8SFG dual gate ox CMOS Logic - 1 layer poly - 6 layer copper
209. 200mm - 130nm - IBM - 8SFG dual gate ox CMOS Logic - 1 layer poly - 7 layer copper
210. 200mm - 130nm - IBM - 8SFG dual gate ox CMOS Logic - 1 layer poly - 8 layer copper
211. 200mm - 130nm - IBM - 9S dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiLK ILD
212. 200mm - 130nm - IBM - 9S dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - SiLK ILD
213. 200mm - 130nm - IBM - 9S dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - SiLK ILD
214. 200mm - 130nm - Infineon - RFCMOS - 1 layer poly - 4 copper and 2 aluminum layers with MIM
215. 200mm - 130nm - Intel - CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
216. 200mm - 130nm - Intel - ETOX VIII Flash - 2 layer poly - 3 layer aluminum
217. 200mm - 130nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
218. 200mm - 130nm - ST Micro - BiCMOS 9 - 7 layer copper - FSG ILD
219. 200mm - 130nm - ST Micro - BiCMOS 9 - 7 layer copper with MIM - FSG ILD
220. 200mm - 130nm - TI - CMOS Logic - 1 layer poly - 5 layer copper - FSG ILD
221. 200mm - 130nm - TI - CMOS Logic - 1 layer poly - 5 layer copper with 1 layer aluminum - FSG ILD
222. 200mm - 130nm - TI - CMOS Logic - 1 layer poly - 6 layer copper with 1 layer aluminum - FSG ILD
223. 200mm - 130nm - Toshiba - NAND Flash - 3 layer poly - 1 tungsten and 2 aluminum layers
224. 200mm - 130nm - Tower - TS13SL dual gate oixde CMOS logic - 1 layer poly - 6 layer copper - FSG ILD
225. 200mm - 130nm - Tower - TS13SL dual gate oixde CMOS logic - 1 layer poly - 7 layer copper - FSG ILD
226. 200mm - 130nm - Tower - TS13SL dual gate oixde CMOS logic - 1 layer poly - 8 layer copper - FSG ILD
227. 200mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
228. 200mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 copper, 1 aluminum layer - FSG ILD
229. 200mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
230. 200mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
231. 200mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
232. 200mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 6 layer copper with 1 aluminum layer - FSG ILD
233. 200mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD

234. 200mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
235. 200mm - 120nm - Samsung - NAND Flash - 4 layer poly - 1 tungsten and 1 aluminum layer
236. 200mm - 120nm - Samsung - SRAM - 1 layer poly - 4 copper layers
237. 200mm - 110nm - Samsung - DRAM - 7 layer poly - 3 layer metal (1W + 2Al)
238. 200mm - 110nm - Toshiba - TC280 dual gate ox CMOS with trench DRAM - 7 layer copper
239. 200mm - 110nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
240. 200mm - 110nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
241. 200mm - 110nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
242. 200mm - 110nm - TSMC - Floating Gate NOR Flash - 3 level metal
243. 200mm - 90nm - AMD - dual gate ox strained silicon CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD - SOI
244. 200mm - 90nm - Intel - ETOX IX Flash - 2 layer poly - 3 layer copper with aluminum bond pads
245. 200mm - 90nm - Samsung - DRAM - 7 layer poly - 3 layer metal (1W + 2Al)
246. 200mm - 90nm - Samsung - NAND Flash - 4 layer poly - 1 tungsten and 1 aluminum layer
247. 200mm - 90nm - Spansion - Floating Gate NOR Flash
248. 200mm - 90nm - Spansion - Mirror Bit NOR Flash
249. 200mm - 90nm - Toshiba - NAND Flash - 3 layer poly - 1 tungsten and 2 aluminum layers
250. 300mm - 250nm - TI - LBC7 BiCMOS - 2 layer poly - 3 layer aluminum
251. 300mm - 150nm - Chartered - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
252. 300mm - 150nm - Samsung NAND Flash - 7 layer poly - 1 tungsten and 1 aluminum layer
253. 300mm - 150nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
254. 300mm - 150nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
255. 300mm - 150nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
256. 300mm - 150nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
257. 300mm - 150nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer aluminum - FSG ILD
258. 300mm - 130nm - Chartered - dual gate oxide CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
259. 300mm - 130nm - IBM - 8HP SiGe BiCMOS - 6 layer copper with single MIM and TaN resistor
260. 300mm - 130nm - IBM - 8HP SiGe BiCMOS - 7 layer copper with single MIM and TaN resistor
261. 300mm - 130nm - IBM - 8HP SiGe BiCMOS - 8 layer copper with single MIM and TaN resistor
262. 300mm - 130nm - IBM - 8RF RF CMOS - with Cu-Cu-Cu-Al-CU-Al and single MIM and TaN resistor
263. 300mm - 130nm - IBM - 8SFG dual gate ox CMOS Logic - 1 layer poly - 6 layer copper
264. 300mm - 130nm - IBM - 8SFG dual gate ox CMOS Logic - 1 layer poly - 7 layer copper
265. 300mm - 130nm - IBM - 8SFG dual gate ox CMOS Logic - 1 layer poly - 8 layer copper

266. 300mm - 130nm - IBM - 9S dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiLK ILD
267. 300mm - 130nm - IBM - 9S dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - SiLK ILD
268. 300mm - 130nm - IBM - 9S dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - SiLK ILD
269. 300mm - 130nm - Intel - CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
270. 300mm - 130nm - Renesas - dual gate oxide CMOS Logic - 1 poly layer - 1 tungsten, 5 copper and 1 aluminum layer
271. 300mm - 130nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
272. 300mm - 130nm - TI - CMOS Logic - 1 layer poly - 5 layer copper - FSG ILD
273. 300mm - 130nm - TI - CMOS Logic - 1 layer poly - 5 layer copper with 1 layer aluminum - FSG ILD
274. 300mm - 130nm - TI - CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
275. 300mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
276. 300mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
277. 300mm - 130nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
278. 300mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
279. 300mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
280. 300mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
281. 300mm - 130nm - UMC - L130 dual gate ox CMOS Logic - 1 layer poly - 8 copper and 1 aluminum layers - FSG ILD
282. 300mm - 120nm - Samsung NAND Flash - 4 layer poly - 1 tungsten and 1 aluminum layer
283. 300mm - 110nm - Samsung DRAM - 7 layer poly - 3 layer metal (1W + 2Al)
284. 300mm - 110nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - FSG ILD
285. 300mm - 110nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - FSG ILD
286. 300mm - 110nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - FSG ILD
287. 300mm - 90nm - AMD - dual gate ox strained silicon CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD - SOI
288. 300mm - 90nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
289. 300mm - 90nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
290. 300mm - 90nm - Chartered - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
291. 300mm - 90nm - Freescale - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiOC ILD
292. 300mm - 90nm - Freescale - triple gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiOC ILD - SOI
293. 300mm - 90nm - IBM - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD

294. 300mm - 90nm - IBM - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
295. 300mm - 90nm - IBM - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
296. 300mm - 90nm - IBM - dual gate oxide - 1 layer poly - 9 layer copper - SiOC ILD - SOI
297. 300mm - 90nm - Intel - SiGe Communications process
298. 300mm - 90nm - Intel - Strained Silicon CMOS Logic - 1 layer poly - 7 layer copper - SiOC ILD
299. 300mm - 90nm - Samsung - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
300. 300mm - 90nm - Samsung - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
301. 300mm - 90nm - Samsung - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
302. 300mm - 90nm - Samsung - DRAM - RCAT - 7 layer poly - 3 layer metal (1W + 2Al)
303. 300mm - 90nm - Samsung - eDRAM - 8 copper layers and 1 aluminum layer
304. 300mm - 90nm - Samsung - NAND Flash - 4 layer poly - 2 tungsten and 1 aluminum layers
305. 300mm - 90nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiOC ILD
306. 300mm - 90nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
307. 300mm - 90nm - Sony - eDRAM - 4 poly layer - 5 copper and 1 aluminum layer - SiOC/FSG ILD
308. 300mm - 90nm - Sony - eDRAM - 4 poly layer - 11 layer copper - SiOC/FSG ILD
309. 300mm - 90nm - TI - dual gate oxide CMOS Logic - 1 layer poly - 5 layer copper and 1 layer aluminum - SiOC ILD
310. 300mm - 90nm - TI - dual gate oxide CMOS Logic - 1 layer poly - 6 layer copper - SiOC ILD
311. 300mm - 90nm - TI - dual gate oxide CMOS Logic - 1 layer poly - 6 layer copper and 1 layer aluminum - SiOC ILD
312. 300mm - 90nm - TI - dual gate oxide CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
313. 300mm - 90nm - Toshiba - NAND Flash - 4 layer poly - 1 tungsten and 1 aluminum layers
314. 300mm - 90nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper and 1 aluminum layer- SiOC ILD
315. 300mm - 90nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - SiOC ILD
316. 300mm - 90nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - SiOC ILD
317. 300mm - 90nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
318. 300mm - 90nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 9 copper and 1 aluminum layer - SiOC ILD
319. 300mm - 90nm - TSMC - triple gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
320. 300mm - 90nm - TSMC - FPGA process with Flash - 1 layer poly - 9 layer copper - SiOC ILD
321. 300mm - 90nm - TSMC - triple gate ox RFCMOS Logic - 2 layer poly - 9 layer copper - SiOC ILD
322. 300mm - 90nm - UMC - L90 dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - SiOC ILD

323. 300mm - 90nm - UMC - L90 dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - SiOC ILD
324. 300mm - 90nm - UMC - L90 dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
325. 300mm - 90nm - UMC - L90 dual gate ox CMOS Logic - 1 layer poly - 9 copper and 1 aluminum layer - SiOC ILD
326. 300mm - 80nm - Samsung - DRAM RCAT + MESH - 7 layer poly - 3 layer metal (1W + 2Al)
327. 300mm - 73nm - Samsung - NAND Flash - 4 layer poly - 1 tungsten and 2 aluminum layers
328. 300mm - 70nm - Samsung - DRAM - S-RCAT + MESH 7 layer poly - 3 layer metal (1W + 2Al)
329. 300mm - 70nm - Toshiba - NAND Flash - 4 layer poly - 1 tungsten and 2 aluminum layers
330. 300mm - 65nm - AMD - Strained Silicon dual gate ox SOI CMOS - 1 layer poly - 10 layer copper - SiOC ILD
331. 300mm - 65nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 7 layer copper - SiOC ILD
332. 300mm - 65nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 8 layer copper - SiOC ILD
333. 300mm - 65nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
334. 300mm - 65nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
335. 300mm - 65nm - Chartered - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
336. 300mm - 65nm - Freescale - dual gate ox CMOS logic - 1 layer poly - 7 layer copper with MIM caps - SiOC ILD
337. 300mm - 65nm - IBM - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
338. 300mm - 65nm - IBM - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
339. 300mm - 65nm - IBM - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
340. 300mm - 65nm - Intel - Strained Silicon CMOS Logic - 1 layer poly - 8 layer copper - SiOC ILD
341. 300mm - 65nm - Samsung - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
342. 300mm - 65nm - Samsung - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
343. 300mm - 65nm - Samsung - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
344. 300mm - 65nm - Samsung - DRAM - S-RCAT + MESH 7 layer poly - 3 layer metal (1W + 2Al)
345. 300mm - 65nm - Samsung - NAND Flash - 4 layer poly - 1 tungsten and 2 aluminum layers
346. 300mm - 65nm - SMIC - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
347. 300mm - 65nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiOC ILD
348. 300mm - 65nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - SiOC ILD
349. 300mm - 65nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - SiOC ILD

350. 300mm - 65nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
351. 300mm - 65nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
352. 300mm - 65nm - UMC - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
353. 300mm - 57nm - Samsung - DRAM - U_RCAT + MESH 7 layer poly - 3 layer metal (2Cu + 1Al)
354. 300mm - 56nm - Samsung - DRAM - U_RCAT + MESH 7 layer poly - 3 layer metal (2Al + 1W)
355. 300mm - 56nm - Toshiba - NAND Flash - 4 layer poly - 1 tungsten layer and 2 aluminum layers
356. 300mm - 55nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 6 layer copper - SiOC ILD
357. 300mm - 55nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 7 layer copper - SiOC ILD
358. 300mm - 55nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper - SiOC ILD
359. 300mm - 55nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 8 layer copper and 1 layer aluminum - SiOC ILD
360. 300mm - 55nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
361. 300mm - 55nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
362. 300mm - 55nm - STMicro - dual gate ox CMOS logic - 1 layer poly - 7 layer copper with MIM caps - SiOC ILD
363. 300mm - 51nm - Samsung - NAND Flash - 4 layer poly - 1 tungsten and 2 aluminum layers
364. 300mm - 45nm - AMD - Strained Silicon dual gate ox SOI CMOS - 1 layer poly - 10 layer copper - SiOC ILD
365. 300mm - 45nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
366. 300mm - 45nm - Chartered - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
367. 300mm - 45nm - Chartered - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
368. 300mm - 45nm - Freescale - low power triple gate ox CMOS - 1 layer poly - 9 copper layers - SiOC ILD
369. 300mm - 45nm - Global Foundries - dual gate ox CMOS logic on SOI - 1 layer poly - 9 layer copper - SiOC ILD
370. 300mm - 45nm - Global Foundries - dual gate ox CMOS logic on SOI - 1 layer poly - 10 layer copper - SiOC ILD
371. 300mm - 45nm - Global Foundries - dual gate ox CMOS logic on SOI - 1 layer poly - 11 layer copper - SiOC ILD
372. 300mm - 45nm - Global Foundries - dual gate ox CMOS logic on Bulk - 1 layer poly - 9 layer copper - SiOC ILD
373. 300mm - 45nm - Global Foundries - dual gate ox CMOS logic on Bulk - 1 layer poly - 10 layer copper - SiOC ILD
374. 300mm - 45nm - Global Foundries - dual gate ox CMOS logic on Bulk - 1 layer poly - 11 layer copper - SiOC ILD

375. 300mm - 45nm - IBM - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
376. 300mm - 45nm - IBM - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
377. 300mm - 45nm - IBM - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
378. 300mm - 45nm - IBM - eDRAM on SOI - 9 layer copper - SiOC ILD
379. 300mm - 45nm - IBM - eDRAM on SOI - 10 layer copper - SiOC ILD
380. 300mm - 45nm - IBM - eDRAM on SOI - 11 layer copper - SiOC ILD
381. 300mm - 45nm - Intel - strained silicon high-k with dual metal gate CMOS - 9 layer copper - SiOC ILD
382. 300mm - 45nm - Samsung - Common Platform - dual gate ox CMOS logic - 1 layer poly - 9 layer copper - SiOC ILD
383. 300mm - 45nm - Samsung - Common Platform - dual gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
384. 300mm - 45nm - Samsung - Common Platform - triple gate ox CMOS logic - 1 layer poly - 10 layer copper - SiOC ILD
385. 300mm - 45nm - Samsung - DRAM - U_RCAT + MESH 7 layer poly - 3 layer metal (2Cu + 1Al)
386. 300mm - 45nm - Toshiba - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
387. 300mm - 45nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
388. 300mm - 45nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
389. 300mm - 45nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 11 layer copper - SiOC ILD
390. 300mm - 45nm - TSMC - triple gate ox CMOS Logic - 1 layer poly - 11 layer copper - SiOC ILD
391. 300mm - 43nm - Toshiba - NAND Flash - 4 layer poly with High-k interlevel - 3 layer copper
392. 300mm - 40nm - Samsung - NAND Flash - 4 layer poly - 3 copper layers
393. 300mm - 40nm - Toshiba - FPGA process with Flash - 1 layer poly - 11 layer copper - SiOC ILD
394. 300mm - 40nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 9 layer copper - SiOC ILD
395. 300mm - 40nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 10 layer copper - SiOC ILD
396. 300mm - 40nm - TSMC - dual gate ox CMOS Logic - 1 layer poly - 11 layer copper - SiOC ILD
397. 300mm - 40nm - TSMC - eDRAM - 9 layer copper - SiOC ILD
398. 300mm - 40nm - TSMC - eDRAM - 10 layer copper - SiOC ILD
399. 300mm - 40nm - TSMC - eDRAM - 11 layer copper - SiOC ILD
400. 300mm - 40nm - TSMC - triple gate ox CMOS Logic - 1 layer poly - 11 layer copper - SiOC ILD
401. 300mm - 40nm - TSMC - FPGA process with Flash - 1 layer poly - 11 layer copper - SiOC ILD
402. 300mm - 40nm - UMC - FPGA process with Flash - 1 layer poly - 11 layer copper - SiOC ILD
403. 300mm - 32nm - Global Foundries - SOI with dual high-k gate ox - 9 layer copper - SiOC ILD

404. 300mm - 32nm - Global Foundries - SOI with dual high-k gate ox - 10 layer copper - SiOC ILD
405. 300mm - 32nm - Global Foundries - SOI with dual high-k gate ox - 11 layer copper - SiOC ILD
406. 300mm - 32nm - IBM - Common Platform - dual high-k gate ox - 9 layer copper - SiOC ILD
407. 300mm - 32nm - IBM - Common Platform - dual high-k gate ox - 10 layer copper - SiOC ILD
408. 300mm - 32nm - IBM - Common Platform - dual high-k gate ox - 11 layer copper - SiOC ILD
409. 300mm - 32nm - IBM - Common Platform - eDRAM with dual high-k gate ox - 9 layer copper - SiOC ILD
410. 300mm - 32nm - IBM - Common Platform - eDRAM with dual high-k gate ox - 10 layer copper - SiOC ILD
411. 300mm - 32nm - IBM - Common Platform - eDRAM with dual high-k gate ox - 11 layer copper - SiOC ILD
412. 300mm - 32nm - IBM - SOI with dual high-k gate oxides - 9 layer copper - SiOC ILD
413. 300mm - 32nm - IBM - SOI with dual high-k gate oxides - 10 layer copper - SiOC ILD
414. 300mm - 32nm - IBM - SOI with dual high-k gate oxides - 11 layer copper - SiOC ILD
415. 300mm - 32nm - IBM - eDRAM on SOI with dual high-k gate oxides - 9 layer copper - SiOC ILD
416. 300mm - 32nm - IBM - eDRAM on SOI with dual high-k gate oxides - 10 layer copper - SiOC ILD
417. 300mm - 32nm - IBM - eDRAM on SOI with dual high-k gate oxides - 11 layer copper - SiOC ILD
418. 300mm - 32nm - Intel - strained silicon high-k with dual metal gate CMOS - 9 layer copper - SiOC ILD
419. 300mm - 32nm - Samsung - PROJECTED TANOS NAND Flash - 4 layer poly - 3 copper layers
420. 300mm - 32nm - Toshiba - PROJECTED NAND Flash - 4 layer poly with High-k interlevel - 3 layer copper
421. 300mm - 32nm - TSMC - dual gate ox CMOS logic - 9 layer copper - SiOC ILD
422. 300mm - 32nm - TSMC - dual gate ox CMOS logic - 10 layer copper - SiOC ILD
423. 300mm - 32nm - TSMC - dual gate ox CMOS logic - 11 layer copper - SiOC ILD
424. 300mm - 32nm - TSMC - dual gate ox with High-k CMOS logic - 9 layer copper - SiOC ILD
425. 300mm - 32nm - TSMC - dual gate ox with High-k CMOS logic - 10 layer copper - SiOC ILD
426. 300mm - 32nm - TSMC - dual gate ox with High-k CMOS logic - 11 layer copper - SiOC ILD
427. 300mm - 28nm - Global Foundries - Common Platform - dual high-k gate ox - 9 layer copper - SiOC ILD
428. 300mm - 28nm - Global Foundries - Common Platform - dual high-k gate ox - 10 layer copper - SiOC ILD
429. 300mm - 28nm - Global Foundries - Common Platform - dual high-k gate ox - 11 layer copper - SiOC ILD
430. 300mm - 28nm - IBM - Common Platform - dual high-k gate ox - 9 layer copper - SiOC ILD
431. 300mm - 28nm - IBM - Common Platform - dual high-k gate ox - 10 layer copper - SiOC ILD

432. 300mm - 28nm - IBM - Common Platform - dual high-k gate ox - 11 layer copper - SiOC ILD
433. 300mm - 28nm - TSMC - dual gate ox CMOS logic - 9 layer copper - SiOC ILD
434. 300mm - 28nm - TSMC - dual gate ox CMOS logic - 10 layer copper - SiOC ILD
435. 300mm - 28nm - TSMC - dual gate ox CMOS logic - 11 layer copper - SiOC ILD
436. 300mm - 28nm - TSMC - dual gate ox with High-k CMOS logic - 9 layer copper - SiOC ILD
437. 300mm - 28nm - TSMC - dual gate ox with High-k CMOS logic - 10 layer copper - SiOC ILD
438. 300mm - 28nm - TSMC - dual gate ox with High-k CMOS logic - 11 layer copper - SiOC ILD
439. 300mm - 28nm - TSMC - eDRAM with High-k CMOS logic - 9 layer layer - SiOC ILD
440. 300mm - 28nm - TSMC - eDRAM with High-k CMOS logic - 10 layer layer - SiOC ILD
441. 300mm - 28nm - TSMC - eDRAM with High-k CMOS logic - 11 layer layer - SiOC ILD
442. 300mm - 22nm - Intel - PROJECTED strained silicon high-k with dual metal gate CMOS - 10 layer copper - SiOC ILD
443. 300mm - 22nm - Samsung - PROJECTED TANOS NAND Flash - 4 layer poly - 3 copper layers
444. 300mm - 22nm - TSMC - PROJECTED dual gate ox with High-k CMOS logic - 9 layer copper - SiOC ILD
445. 300mm - 22nm - TSMC - PROJECTED dual gate ox with High-k CMOS logic - 10 layer copper - SiOC ILD
446. 300mm - 22nm - TSMC - PROJECTED dual gate ox with High-k CMOS logic - 11 layer copper - SiOC ILD
447. 300mm - 15nm - Intel - PROJECTED strained silicon high-k with dual metal gate CMOS - 11 layer copper
448. 300mm - 15nm - Samsung - PROJECTED TANOS NAND Flash - 4 layer poly - 3 copper layers
449. 450mm - 22nm - Intel - PROJECTED strained silicon high-k with dual metal gate CMOS - 10 layer copper - SiOC ILD
450. 450mm - 22nm - Samsung - PROJECTED TANOS NAND Flash - 4 layer poly - 3 copper layers
451. 450mm - 15nm - Intel - PROJECTED strained silicon high-k with dual metal gate CMOS - 12 layer copper
452. 450mm - 15nm - Samsung - PROJECTED TANOS NAND Flash - 4 layer poly - 3 copper layers